

Radiation Hardened 8-Input NAND Gate

The Radiation Hardened ACS30MS is an 8-Input NAND Gate. A HIGH level on all inputs results in a LOW level on the \bar{Y} output. A LOW level on any input results in a HIGH level on the \bar{Y} output. All inputs are buffered and the outputs are designed for balanced propagation delay and transition times.

The ACS30MS is fabricated on a CMOS Silicon on Sapphire (SOS) process, which provides an immunity to Single Event Latch-up and the capability of highly reliable performance in any radiation environment. These devices offer significant power reduction and faster performance when compared to ALSTTL types.

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed below must be used when ordering.

Detailed Electrical Specifications for the ACS30MS are contained in SMD 5962-98631. A “hot-link” is provided on our homepage for downloading.
<http://www.intersil.com/spacedefense/spaceselect.htm>

Features

- QML Qualified Per MIL-PRF-38535 Requirements
- 1.25 Micron Radiation Hardened SOS CMOS
- Radiation Environment
 - Latch-Up Free Under Any Conditions
 - Total Dose (Max.) 3×10^5 RAD(Si)
 - SEU Immunity $<1 \times 10^{-10}$ Errors/Bit/Day
 - SEU LET Threshold $>100\text{MeV}/(\text{mg}/\text{cm}^2)$
- Input Logic Levels. $V_{IL} = (0.3)(V_{CC})$, $V_{IH} = (0.7)(V_{CC})$
- Output Current $\pm 12\text{mA}$ (Min)
- Quiescent Supply Current $5.0\mu\text{A}$ (Max)
- Propagation Delay 16ns (Max)

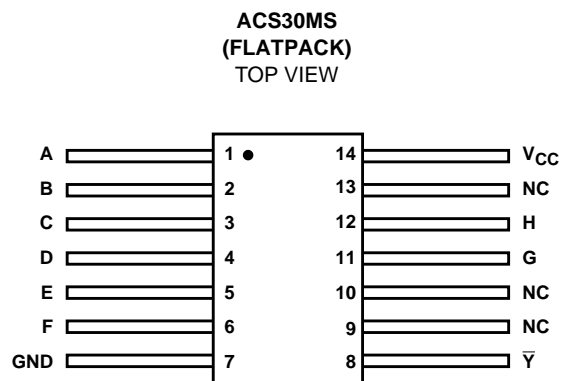
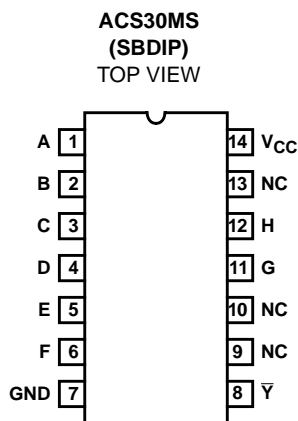
Applications

- High Speed Control Circuits
- Sensor Monitoring
- Low Power Designs

Ordering Information

ORDERING NUMBER	INTERNAL MARKETING NUMBER	TEMP. RANGE (°C)	PACKAGE	DESIGNATOR
5962F9863101VCC	ACS30DMSR-03	-55 to 125	14 Ld SBDIP	CDIP2-T14
ACS21D/SAMPLE-03	ACS30D/SAMPLE-03	25	14 Ld SBDIP	CDIP2-T14
5962F9863101VXC	ACS30KMSR-03	-55 to 125	14 Ld Flatpack	CDFP3-F14
ACS21K/SAMPLE-03	ACS30K/SAMPLE-03	25	14 Ld Flatpack	CDFP3-F14
5962F9863101V9A	ACS30HMSR-03	25	Die	NA

Pinouts



Die Characteristics

DIE DIMENSIONS:

Size: 2390 μ m x 2390 μ m (94 mils x 94 mils)
 Thickness: 525 μ m \pm 25 μ m (20.6 mils \pm 1 mil)
 Bond Pad: 110 μ m x 110 μ m (4.3 x 4.3 mils)

METALLIZATION: Al

Metal 1 Thickness: 0.7 μ m \pm 0.1 μ m
 Metal 2 Thickness: 1.0 μ m \pm 0.1 μ m

SUBSTRATE POTENTIAL

Unbiased Insulator

PASSIVATION:

Type: Phosphorous Silicon Glass (PSG)
 Thickness: 1.30 μ m \pm 0.15 μ m

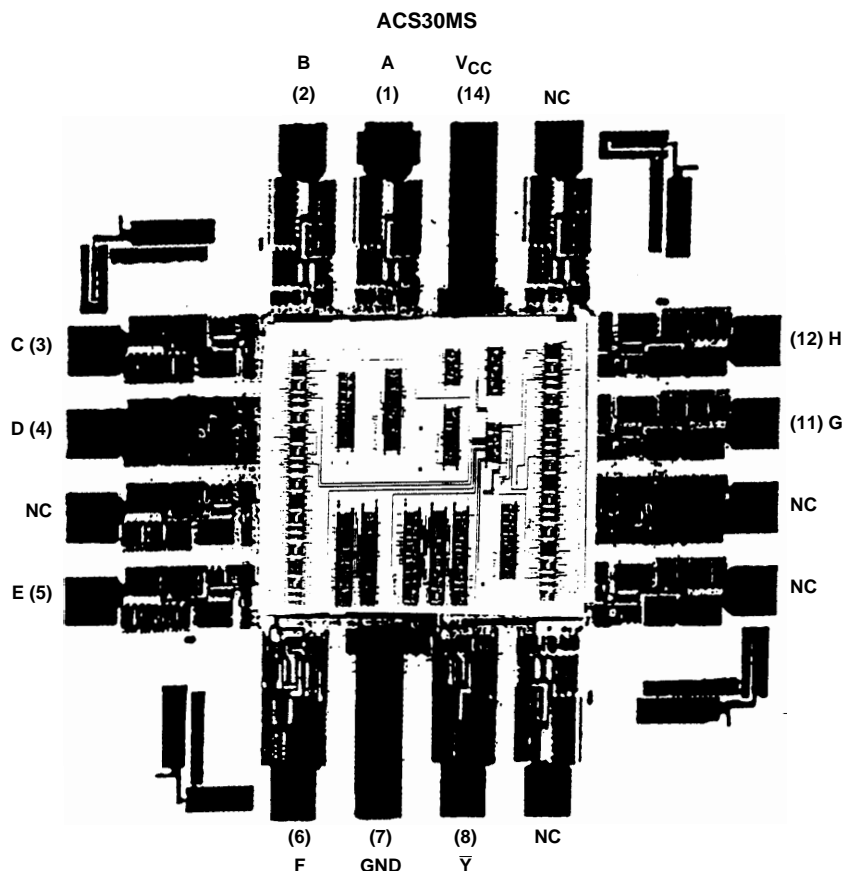
SPECIAL INSTRUCTIONS

Bond V_{CC} First

ADDITIONAL INFORMATION:

Worst Case Current Density: <2.0 x 10⁵ A/cm²
 Transistor Count: 86

Metallization Mask Layout



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